

# **HAT2105T**

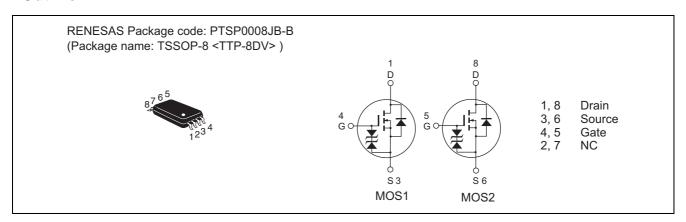
# Silicon N Channel MOS FET High Speed Power Switching

REJ03G0384-0200 Rev.2.00 Aug 06, 2007

#### **Features**

- Low on-resistance
- Capable of 4 V gate drive
- High density mounting

#### **Outline**



## **Absolute Maximum Ratings**

 $(Ta = 25^{\circ}C)$ 

Item	Symbol	Ratings	Unit
Drain to source voltage	V <sub>DSS</sub>	200	V
Gate to source voltage	V <sub>GSS</sub>	±15	V
Drain current	I <sub>D</sub>	0.5	A
Drain peak current	I <sub>D</sub> (pulse) <sup>Note1</sup>	2	А
Body-drain diode reverse drain current	I <sub>DR</sub>	0.5	A
Channel dissipation	Pch <sup>Note 2</sup>	1	W
	Pch <sup>Note 3</sup>	1.5	W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. PW  $\leq$  10  $\mu$ s, duty cycle  $\leq$  1 %

- 2. 1 Drive operation ; When using the glass epoxy board (FR4 40 x 40 x 1.6 mm), PW  $\leq$  10 s
- 3. 2 Drive operation; When using the glass epoxy board (FR4 40 x 40 x 1.6 mm), PW  $\leq$  10 s

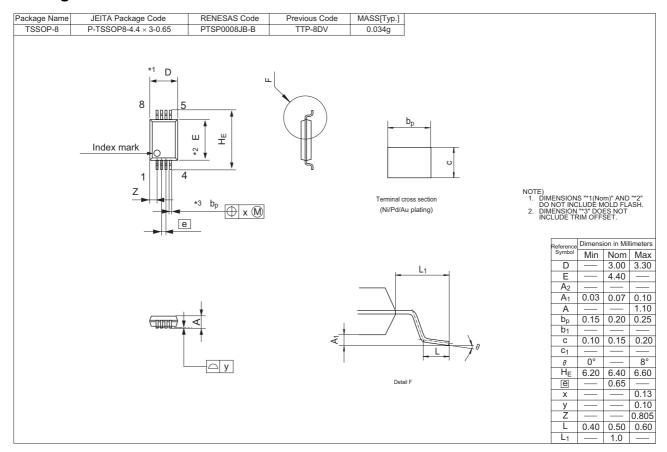
# **Electrical Characteristics**

 $(Ta = 25^{\circ}C)$ 

Item	Symbol	Min.	Тур.	Max.	Unit	Test Conditions
Drain to source breakdown voltage	V <sub>(BR)DSS</sub>	200	_	_	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	±15	_	_	V	$I_G = \pm 100 \ \mu A, \ V_{DS} = 0$
Gate to source leak current	I <sub>GSS</sub>	_	_	±10	μΑ	$V_{GS} = \pm 12 \text{ V}, V_{DS} = 0$
Zero gate voltage drain current	I <sub>DSS</sub>		1	5	μΑ	$V_{DS} = 200 \text{ V}, V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	1.0	1	2.1	V	$V_{DS} = 10 \text{ V}, I_D = 1 \text{ mA}$
Static drain to source on state	R <sub>DS(on)</sub>	_	1.6	2.2	Ω	$I_D = 0.5 \text{ A}, V_{GS} = 10 \text{ V}^{\text{Note4}}$
resistance	R <sub>DS(on)</sub>	_	1.9	2.7	Ω	$I_D = 0.5 \text{ A}, V_{GS} = 4 \text{ V}^{\text{Note4}}$
	R <sub>DS(on)</sub>	_	2.4	5.5	Ω	$I_D = 2 A$ , $V_{GS} = 5 V^{Note4}$
Forward transfer admittance	y <sub>fs</sub>	0.56	0.86	_	S	$I_D = 0.5 \text{ A}, V_{DS} = 10 \text{ V}^{\text{Note4}}$
Input capacitance	Ciss	_	120	_	pF	V <sub>DS</sub> = 10 V
Output capacitance	Coss	_	29	_	pF	$V_{GS} = 0$
Reverse transfer capacitance	Crss	_	10	_	pF	f = 1 MHz
Turn-on delay time	t <sub>d(on)</sub>	_	10	_	ns	$V_{GS} = 5 \text{ V}, I_D = 0.5 \text{ A}$
Rise time	t <sub>r</sub>	_	14	_	ns	$V_{DD} \cong 30 \text{ V}$
Turn-off delay time	t <sub>d(off)</sub>	_	24	_	ns	
Fall time	t <sub>f</sub>	_	9	_	ns	
Body-drain diode forward voltage	$V_{DF}$	_	0.9	1.4	V	$I_F = 0.5 \text{ A}, V_{GS} = 0^{\text{Note4}}$

Notes: 4. Pulse test

## **Package Dimensions**



## **Ordering Information**

Part No.	Quantity	Shipping Container
HAT2105T-EL-E	3000 pcs	Taping

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